

[PIXEL STRUCTURE AND FABRICATING METHOD THEREOF]

Abstract

A pixel structure and a fabricating method thereof are described. The method comprises forming a conductive layer, a data line and a source/drain at the same time. The conductive layer has a coupling portion and a connecting portion. The coupling portion is used as a top electrode of a pixel storage capacitor, and the connecting portion connects the coupling portion and the drain. Thereafter, a contact window is defined on the connecting portion, and a pixel electrode formed subsequently can be electrically connected to the connecting portion through the contact window. Thus, the pixel electrode, the conductive layer (includes the coupling portion) and the drain are electrically connected each other. Since the contact window is not formed above the pixel storage capacitor, the leakage of the pixel storage capacitor will not occur when the etching process of the contact window etches away the gate insulating layer.